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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Charles M. McKenna et al.
Serial No: 09/602,059
Confirmation No: 9493
Filed: June 23, 2000
For: ION IMPLANTER HAVING TWO-STAGE DECELERATION
BEAMLINE
Examiner: Mary A. El-Shammaa
Art Unit: 2881

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Cheryl A. Putcell
Cheryl Putcell

Commissioner for Patents
Washington, D.C. 20231

Sir:

AMENDMENT

In response to the Office Action mailed November 6, 2002, please amend the above-identified application as follows.

In the Claims

Please amend claims 1, 15, 30, 37, 45 and 52 to read as follows. Marked-up copies of the amended claims, with changes indicated by bracketing and underlining, are enclosed.

1. (As Amended) An ion implanter comprising:

A¹
an ion source for generating an ion beam at a first voltage V_0 ;
an analyzer for separating unwanted components from said ion beam;
a beam transport device for transporting said ion beam through said
analyzer at a first transport energy;